

SILICON BRIDGE RECTIFIERS

TMBS4S1

FEATURES

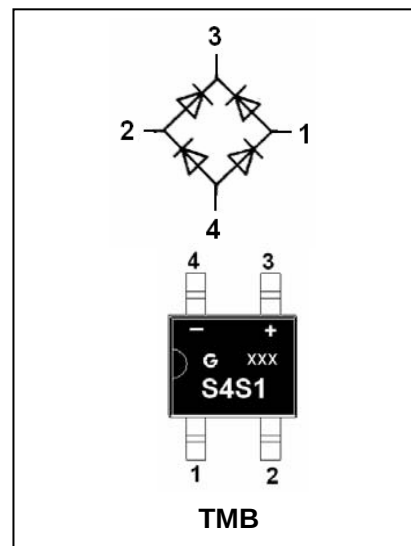
- Schottky barrier rectifier
- Guardring protection
- Low forward voltage
- Reverse energy tested
- High current capability
- Extremely low thermal resistance



Lead-free

APPLICATION

- CFL rectify circuit
- Charge rectify circuit



MAXIMUM RATING (operating temperature range applies unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	40	V
V_{RMS}	Maximum RMS voltage	28	V
V_{DC}	DC Blocking Voltage	40	V
$I_{F(AV)}$	Average Forward Rectified Current@ $T_A=25^{\circ}C$	1.0	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half Sine-wave	30	A
$R_{\theta JA}$	Thermal Resistance	28	$^{\circ}C/W$
T_j T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Test conditions	Value	Unit
I_R	Reverse Current	$V_{RM}=V_{RRM}, T_A=25^{\circ}C$	0.4	mA
		$V_{RM}=V_{RRM}, T_A=100^{\circ}C$	10	
V_F	Forward Voltage (NOTE1)	$I_F=1.0A, T_A=25^{\circ}C$	0.5	V

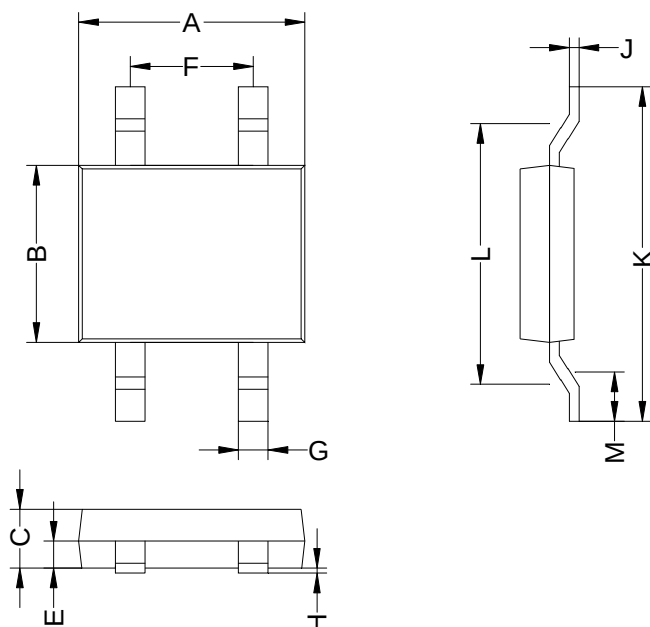
NOTE: 1.Pulse test: Pulse width 300us,duty cycle 1 %

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PACKAGE OUTLINE DIMENSIONS

TMB



TMB		
Dim	Min	Max
A	4.50	4.70
B	3.60	3.80
C	1.20 TYP.	
E	0.45	0.65
F	2.60	2.80
G	0.60	0.80
H	0.05	0.15
J	0.20 TYP.	
K	6.60	7.00
L	5.10	5.50
M	0.90	1.10
All Dimensions in mm		